● PRINTER RUSH ●
(PTO ASSISTANCE)

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REV 10/04

Description

Method and apparatus for the arrangement of contact-making elements of components of an integrated circuit, computer-readable storage medium and program element

The invention relates to a method and an apparatus for the arrangement of contact-making elements of components of an integrated circuit, a computer-readable storage medium and a program element.

Further advancing miniaturization in silicon microelectronics is also accompanied by an increase in the requirements made of lithography methods used in this context.

The task of a lithography method is to produce a multiplicity of resist structures on a silicon wafer in dimensionally true, positionally correct and defect-free fashion. Criteria for the performance of a lithography method are the minimum feature size that can be achieved, the line width variation, the positional error variation and also the defect density. The minimum structural dimension that can be achieved ("critical dimension", CD), in particular, is essential with regard to a high integration density desired.

A lithography mask is used, inter alia, for making electrical contact with an arrangement of processed integrated components of a silicon chip. For this purpose, a component with which contact is to be made is electrically coupled to an electrically conductive contact-making element, the contact-making element often having a square cross section. As the structural dimension of an integrated circuit is reduced, the side length of the contact-making element is also scaled to ever smaller dimensions, a reduction of a side length ~~of a square contact-making element being incorporated~~ of a square contact-making element being incorporated